

A decorative graphic on the left side of the slide, consisting of a vertical black line intersecting a horizontal black line. To the left of the intersection are three overlapping squares: a blue one on top, a red one on the left, and a yellow one on the bottom.

# Solid-State Radiation Sensors

Federico Ravotti

*TS-LEA-RAD*

Maurice Glaser, Michael Moll

*PH-DT2-SD*



# Outline



- Introduction;
- Sensor Catalogue;
- Dose Sensors (RadFETs);
- Fluence Sensors (p-i-n and detector diodes);
- Readout Circuitry;
- Integration Issues in the Experiments;
- Conclusions.

# Introduction

- TS-LEA and PH-DT2 have characterized a set of sensors for IEL (Dose) and NIEL ( $\Phi_{eq}$ ) measurement;
- Survey of cumulated Rad. Damage in detector and elect.;
- Sensors suited for the LHC experiments environment;
- “*Sensor Catalogue*” published;
- R&D on sensors is ongoing: OSL,  $n_{th}$  sensors, ...
- Integration into the experiments and their readout is not our responsibility!

# Sensor Catalogue



Address <http://lhc-expt-radmon.web.cern.ch/lhc-expt-radmon/> Go

**LHC Experiment Radiation Monitoring (RADMON)**

[Solid-State Radiation Sensor Group](#)


[Publications](#)

[Link to LHC Machine \(RADWG\)](#)

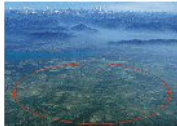
[Link to Tevatron \(CDF, D0\)](#)

[Link to HERA \(H1, HERMES, ZEUS\)](#)

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## Solid-State Radiation Sensor Working Group



### [Sensor Catalogue \(PDF\)](#)

(DATA COMPILATION OF SOLID-STATE SENSORS FOR RADIATION MONITORING)

by

[Federico Ravotti](#) (TS-LEA-RAD), Maurice Glaser and Michael Moll (PH-DT2-SD)

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**Standard RADMON Integrated Packaging 36LD Chip Carrier**

[www.cern.ch/lhc-expt-radmon/](http://www.cern.ch/lhc-expt-radmon/)

# TID (Dose) Sensors



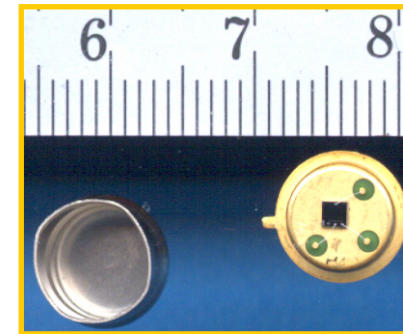
RadFETs: Charge built-up in  $\text{SiO}_2 \rightarrow V_{\text{th}}$  shift proportional to dose

## ➤ Thin-Oxide RadFET dies (0.13-0.25 $\mu\text{m}$ ):

- “low” sensitivity (0.1 Gy) – high dynamic range ( $\sim 100$  kGy);
- Minimize  $\text{SiO}_2$  recombination effects  $\rightarrow$  mixed-LET particle fields;
- Suited for dosimetry in inner-detector regions;
- 850 pcs. at CERN: selection and QA ongoing at CERN.

## ➤ Thick-Oxide RadFET dies (1.6 $\mu\text{m}$ ):

- “high” sensitivity (mGy) – low dynamic range ( $\sim 10$  Gy);
- Measurement in “conventional” ( $\gamma + n$ ) radiation fields.
- Suited for dosimetry in outer-detector regions;
- 100 pcs. at CERN: first 30 to be delivered next week to ATLAS.



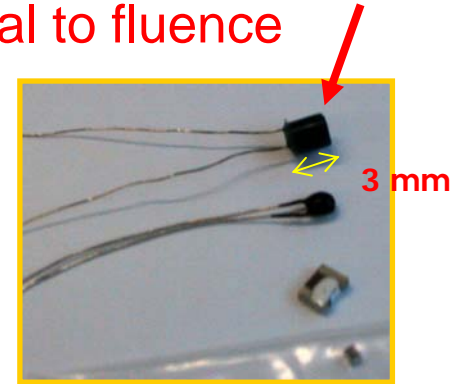
# $\Phi_{eq}$ (Fluence) Sensors



p-i-n diodes: Bulk damage in Si base  $\rightarrow$   $V_F$  shift proportional to fluence

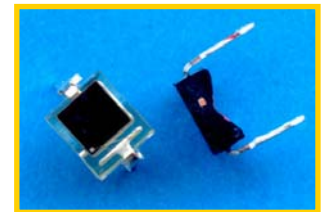
## ➤ High-Sensitivity diodes:

- Range:  $\Phi_{eq} < 2 \times 10^{12} \text{ cm}^{-2}$ ; Sensitivity:  $\sim 2 \times 10^8 \text{ cm}^{-2}/\text{mV}$ ;
- Packaged or Si Crystal ( $\sim 1 \text{ mm}^3$ ) for wire-bonding;
- 100 pcs. at CERN: first 30 to be delivered next week to ATLAS.

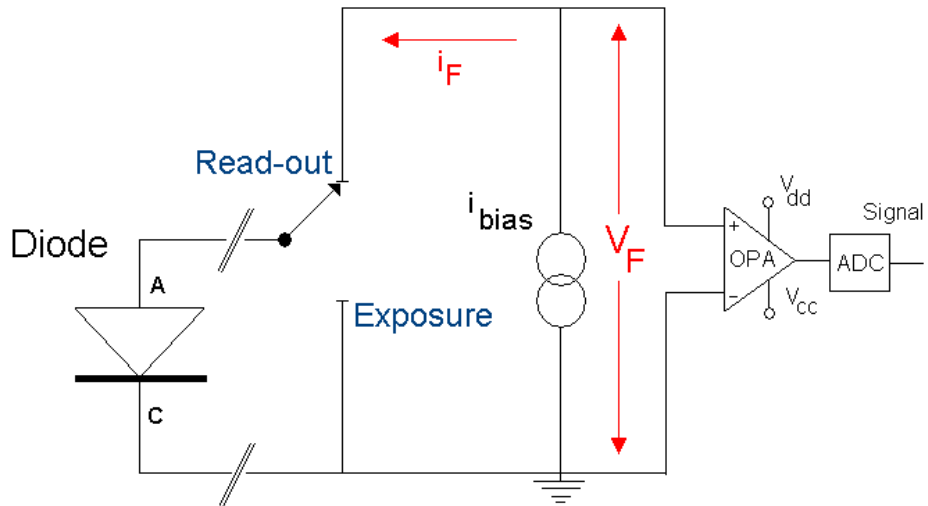


## ➤ Low-Sensitivity diodes:

- Range:  $2 \times 10^{12}$  to  $4 \times 10^{14} \text{ cm}^{-2}$ ; Sensitivity:  $\sim 8 \times 10^9 \text{ cm}^{-2}/\text{mV}$ ;
- Commercial Packaging ( $\sim 5 \text{ mm}^2$ ), no other choices!
- 160 pcs. at CERN pre-selected to guarantee homogeneity.

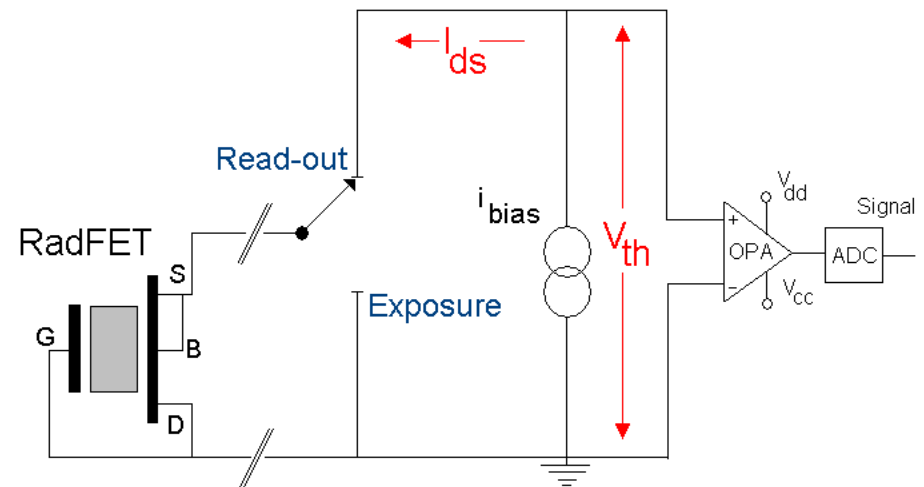


# $\Phi_{eq}$ and TID Readout



- Currents: 100  $\mu$ A to 200  $\mu$ A;
- Time: 5 sec (optimum),  
1 sec (minimum).

- Currents: 1 mA to 25 mA;
- Time: 50 ms (optimum),  
200 ms (maximum).



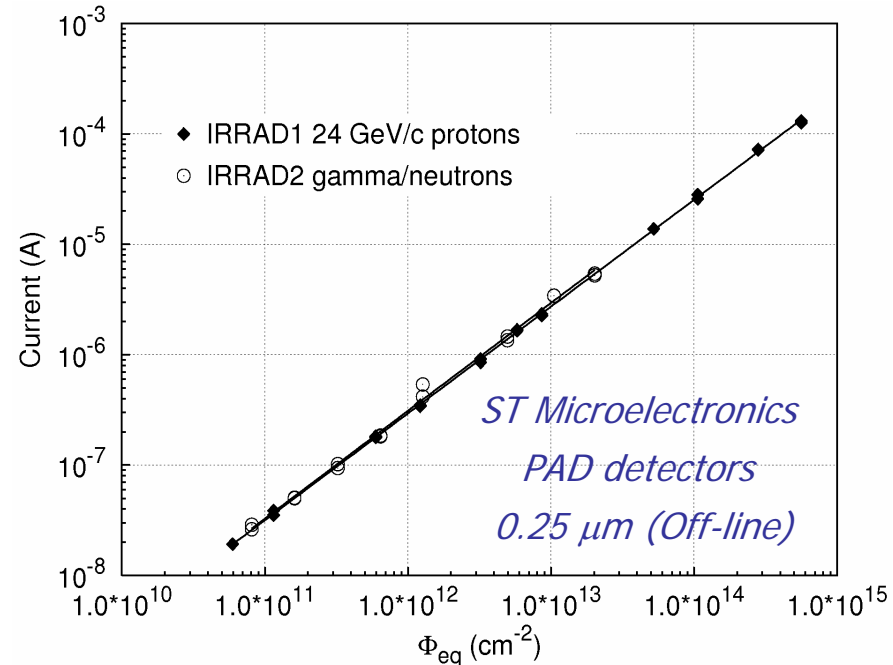
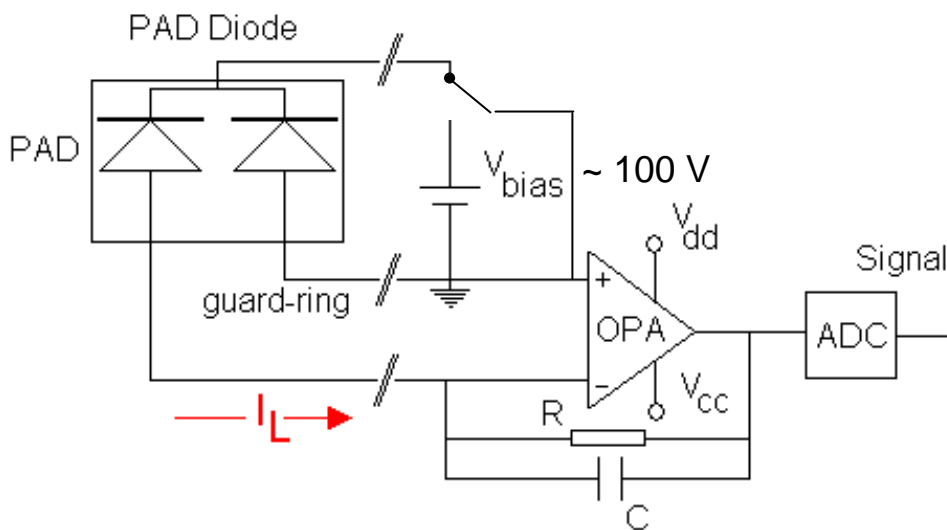
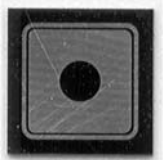
# $\Phi_{eq}$ (Fluence) Sensors



Detector diodes: Bulk damage in Si base  $\rightarrow I_L$  shift proportional to fluence

## ➤ Particle Detector diodes (300 $\mu\text{m}$ ):

- Range:  $1 \times 10^{11}$  to  $5 \times 10^{14} \text{ cm}^{-2}$ ; Sensitivity:  $\sim 4 \times 10^9 \text{ cm}^{-2}/\text{nA}$ ;
- $\sim 60$  bare samples ( $7 \text{ mm}^2$ ) from ST Microelectronics on stock.
- More complicate readout!

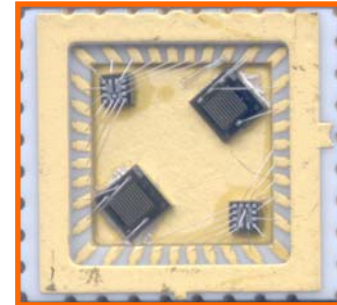
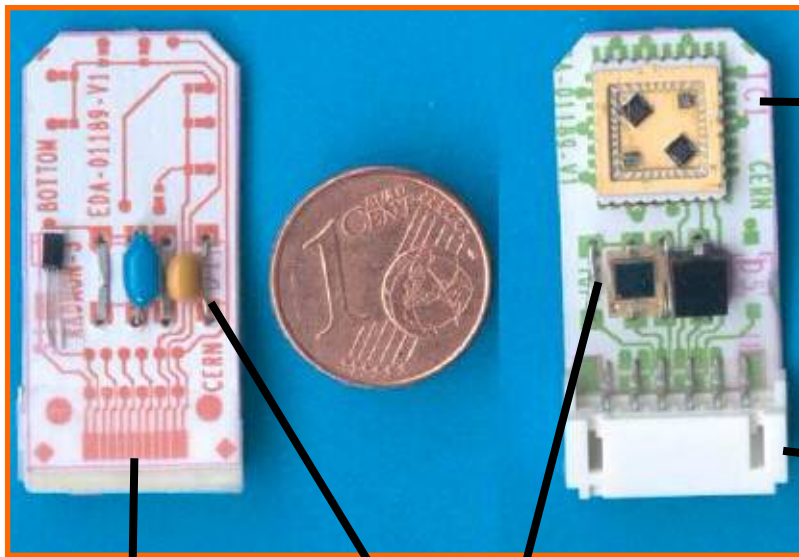




# Integration Issues 1/2



about 30 x 15 x 8 mm PCB



TID sensors  
Package:  
Integration of  
several devices!

The TID sensors can be strongly affected by the surrounding materials

standard connector

## **RADMON BOARD (up to 11 sensors)**

Soldering contacts

$\Phi_{eq}$  Sensors covering 2 dynamic ranges!

+

Temperature sensor

*The sensor carrier can be integrated in “on-line” data acquisition systems but can be also removed and used in “off-line” mode on a laboratory test bench.*

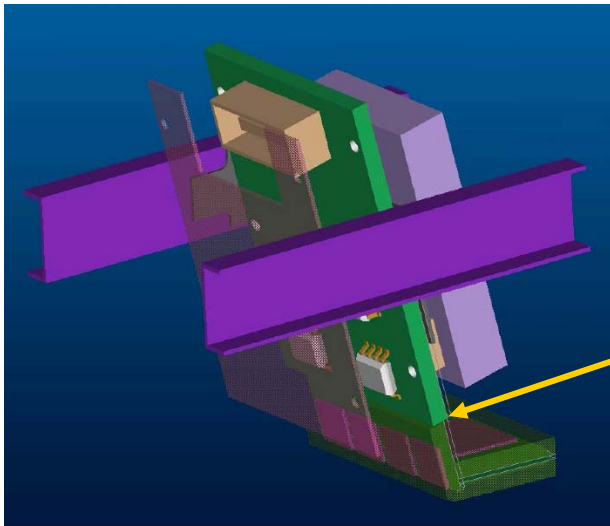
# Integration Issues 2/2



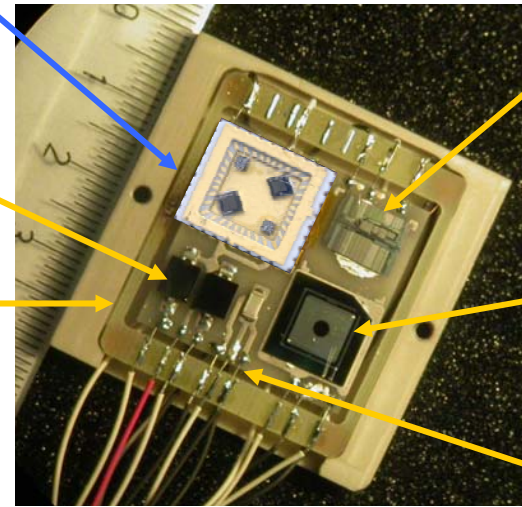
## ATLAS ID (RMSB Hybrid)

4 x RADFETs (.. + High Sens. Pin + ..)

## CMS (BCM 1)



[A. Macpherson, CERN]



BPW34 diodes

PCB with T control

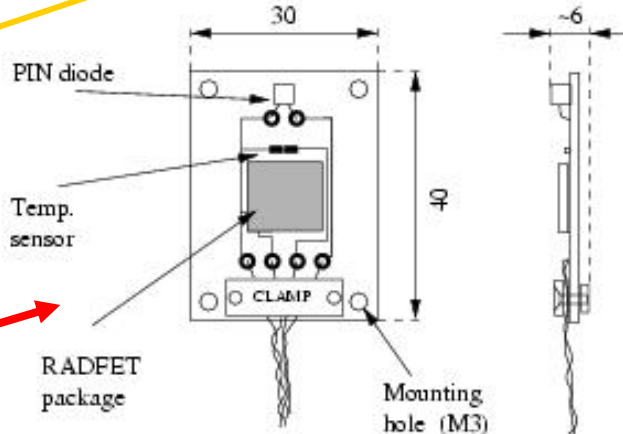
DMILL structure (n<sub>th</sub> damage)

PAD diode

PT1000

[I. Mandic, JSI]

p-i-n diode



## Rest of ATLAS

## ELMB (ADC) + DAQ



General-purpose plug-on I/O module for the monitoring and control of sub-detector front-end equipment



# Conclusions



- A set of sensors for the radiation monitoring (IEL and NIEL) in the LHC Experiment environment is available;
- The sensors for the LHC startup have already been procured. The first sensors are delivered to the Experiments;
- The sensor choice has to take into account: expected type of damage, radiation field intensity and composition;
- The integration remain the responsibility of the Experiments.
- Technical Contacts/Informations: [Maurice.Glaser@cern.ch](mailto:Maurice.Glaser@cern.ch); [Federico.Ravotti@cern.ch](mailto:Federico.Ravotti@cern.ch)

[www.cern.ch/lhc-expt-radmon/](http://www.cern.ch/lhc-expt-radmon/)